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Advanced Etch Technology and Process Integration for Nanopatterning XI

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Contents

v *Conference Committee*

ATOMIC LAYER ETCHING AND NOVEL PLASMA TECHNIQUES

- 12056 02 **Challenge to achieve thermal atomic layer etching of non-volatile materials via stable organometallic complex formation (Invited Paper) [12056-3]**
- 12056 03 **Control of sidewall roughness formation in through-silicon via etch at non-cryogenic temperatures (Invited Paper) [12056-5]**

MATERIALS AND ETCH INTEGRATION

- 12056 04 **Patterning of Ru metal lines at 18nm pitch (Invited Paper) [12056-7]**
- 12056 05 **Tone reversal patterning for advanced technology nodes [12056-9]**

COMPUTATIONAL PATTERNING AND PATTERNING PROCESS CONTROL

- 12056 06 **Dielectric material etch selectivity control in dual-frequency capacitively coupled plasmas with dc-superposition (Invited Paper) [12056-11]**
- 12056 07 **OPC accuracy improvement through deep-learning based etch model [12056-12]**
- 12056 08 **Automated, high throughput optimization of multistep and cyclic etch and deposition processes using SandBox Studio™ AI [12056-13]**

PATTERNING SOLUTIONS FOR EMERGING APPLICATIONS

- 12056 09 **Study of surface interactions for encapsulation of phase change memory materials [12056-17]**

EUV INTEGRATION: JOINT SESSION WITH CONFERENCE 12051 AND 12056

- 12056 0A **Outlook for high-NA EUV patterning: a holistic patterning approach to address upcoming challenges (Invited Paper) [12056-18]**

ADVANCED PATTERNING INTEGRATION

12056 0B **Buried power rail integration for CMOS scaling beyond the 3 nm node (Invited Paper)**
[12056-21]

12056 0C **Middle-of-line plasma dry etch challenges for buried power rail integration** [12056-23]

POSTER SESSION

12056 0D **Mitigation of the etch-induced intra-field overlay contribution** [12056-25]

12056 0E **Creating new multistep etch and deposition processes with recycled etch data using SandBox Studio AI** [12056-26]

12056 0F **Approaches to enable patterning of tight pitches towards high NA EUV** [12056-28]

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